

Dual Bias Resistor Transistors

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the LMUN5211DW1T1 series, two BRT devices are housed in the SOT-363 package which is ideal for low power surface mount applications where board space is at a premium.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted, common for Q₁ and Q₂)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Emitter-Base Breakdown Voltage	V _{EBO}	6	Vdc
Collector Current	I _C	100	mAdc

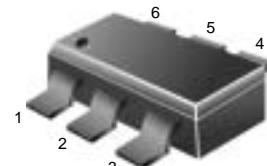
THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C	P _D	187 (Note 1.) 256 (Note 2.)	mW
Derate above 25°C		1.5 (Note 1.) 2.0 (Note 2.)	mW/°C
Thermal Resistance – Junction-to-Ambient	R _{θJA}	670 (Note 1.) 490 (Note 2.)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C	P _D	250 (Note 1.) 385 (Note 2.)	mW
Derate above 25°C		2.0 (Note 1.) 3.0 (Note 2.)	mW/°C
Thermal Resistance – Junction-to-Ambient	R _{θJA}	493 (Note 1.) 325 (Note 2.)	°C/W
Thermal Resistance – Junction-to-Lead	R _{θJL}	188 (Note 1.) 208 (Note 2.)	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

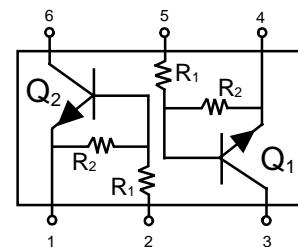
1. FR-4 @ Minimum Pad

2. FR-4 @ 1.0 x 1.0 inch Pad

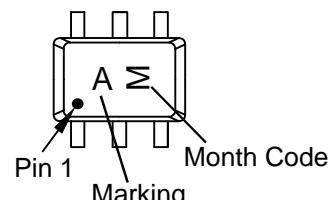
LMUN5211DW1T1G
Series
S-LMUN5211DW1T1G
Series



SC-88/SOT-363



MARKING DIAGRAM



LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
DEVICE MARKING , RESISTOR VALUES AND ORDERING INFORMATION

Device	Package	Marking	R1(K)	R2(K)	Vin(V)	Shipping
LMUN5211DW1T1G	SC88	7A	10	10	-10~+40	3000/Tape&Reel
LMUN5211DW1T3G						10000/Tape&Reel
LMUN5212DW1T1G	SC88	7B	22	22	-10~+40	3000/Tape&Reel
LMUN5212DW1T3G						10000/Tape&Reel
LMUN5213DW1T1G	SC88	7C	47	47	-10~+40	3000/Tape&Reel
LMUN5213DW1T3G						10000/Tape&Reel
LMUN5214DW1T1G	SC88	7D	10	47	-6~+40	3000/Tape&Reel
LMUN5214DW1T3G						10000/Tape&Reel
LMUN5215DW1T1G	SC88	7E	10	∞	-6~+40	3000/Tape&Reel
LMUN5215DW1T3G						10000/Tape&Reel
LMUN5216DW1T1G	SC88	7F	4.7	∞	-6~+30	3000/Tape&Reel
LMUN5216DW1T3G						10000/Tape&Reel
LMUN5230DW1T1G	SC88	7G	1.0	1.0	-10~+10	3000/Tape&Reel
LMUN5230DW1T3G						10000/Tape&Reel
LMUN5231DW1T1G	SC88	7H	2.2	2.2	-10~+12	3000/Tape&Reel
LMUN5231DW1T3G						10000/Tape&Reel
LMUN5232DW1T1G	SC88	7J	4.7	4.7	-10~+30	3000/Tape&Reel
LMUN5232DW1T3G						10000/Tape&Reel
LMUN5233DW1T1G	SC88	7K	4.7	47	-5~+30	3000/Tape&Reel
LMUN5233DW1T3G						10000/Tape&Reel
LMUN5234DW1T1G	SC88	7L	22	47	-8~+40	3000/Tape&Reel
LMUN5234DW1T3G						10000/Tape&Reel
LMUN5235DW1T1G	SC88	7M	2.2	47	-6~+12	3000/Tape&Reel
LMUN5235DW1T3G						10000/Tape&Reel
LMUN5236DW1T1G	SC88	7N	100	100	-10~+40	3000/Tape&Reel
LMUN5236DW1T3G						10000/Tape&Reel
LMUN5237DW1T1G	SC88	7P	47	22	-10~+40	3000/Tape&Reel
LMUN5237DW1T3G						10000/Tape&Reel

LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, common for Q_1 and Q_2)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50 \text{ V}$, $I_E = 0$)	I_{CBO}	—	—	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50 \text{ V}$, $I_B = 0$)	I_{CEO}	—	—	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0 \text{ V}$, $I_C = 0$)	I_{EBO}	—	—	0.5	mAdc
MUN5211DW1T1, G		—	—	0.2	
MUN5212DW1T1, G		—	—	0.1	
MUN5213DW1T1, G		—	—	0.2	
MUN5214DW1T1, G		—	—	0.9	
MUN5215DW1T1, G		—	—	1.9	
MUN5216DW1T1, G		—	—	4.3	
MUN5230DW1T1, G		—	—	2.3	
MUN5231DW1T1, G		—	—	1.5	
MUN5232DW1T1, G		—	—	0.18	
MUN5233DW1T1, G		—	—	0.13	
MUN5234DW1T1, G		—	—	0.2	
MUN5235DW1T1, G		—	—	0.05	
MUN5236DW1T1, G		—	—	0.13	
MUN5237DW1T1, G		—	—		
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	50	—	—	Vdc
Collector-Emitter Breakdown Voltage (Note 3) ($I_C = 2.0 \text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	50	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 200 \mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	6	—	—	Vdc

3. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

ON CHARACTERISTICS (Note 4)

DC Current Gain ($V_{CE} = 10 \text{ V}$, $I_C = 5.0 \text{ mA}$)	MUN5211DW1T1, G MUN5212DW1T1, G MUN5213DW1T1, G MUN5214DW1T1, G MUN5215DW1T1, G MUN5216DW1T1, G MUN5230DW1T1, G MUN5231DW1T1, G MUN5232DW1T1, G MUN5233DW1T1, G MUN5234DW1T1, G MUN5235DW1T1, G MUN5236DW1T1, G MUN5237DW1T1, G	h_{FE}	35 60 80 80 160 160 3.0 8.0 15 80 80 80 80 80	60 100 140 140 350 350 5.0 15 30 200 150 140 150 140	— — — — — — — — — — — — — — —	
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LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
ELECTRICAL CHARACTERISTICS

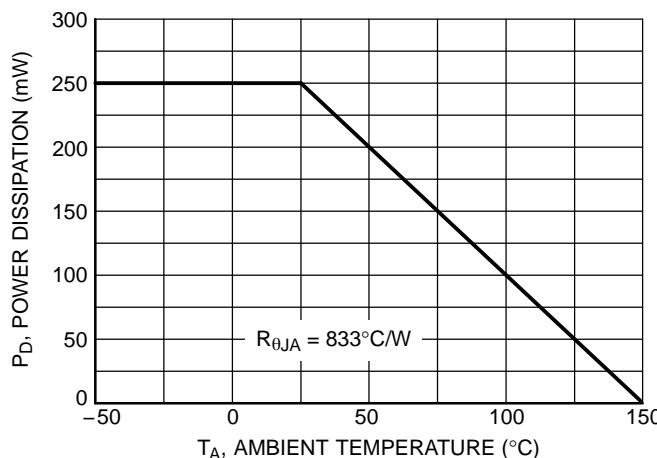
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.3 \text{ mA}$)	MUN5211DW1T1, G MUN5212DW1T1, G MUN5213DW1T1, G MUN5214DW1T1, G MUN5236DW1T1, G MUN5230DW1T1, G MUN5231DW1T1, G MUN5237DW1T1, G MUN5215DW1T1, G MUN5216DW1T1, G MUN5232DW1T1, G MUN5233DW1T1, G MUN5234DW1T1, G MUN5235DW1T1, G	$V_{CE(\text{sat})}$	-	-	0.25	Vdc
($I_C = 10 \text{ mA}$, $I_B = 5 \text{ mA}$)	MUN5211DW1T1, G MUN5212DW1T1, G MUN5213DW1T1, G MUN5214DW1T1, G MUN5236DW1T1, G MUN5230DW1T1, G MUN5231DW1T1, G MUN5237DW1T1, G MUN5215DW1T1, G MUN5216DW1T1, G MUN5232DW1T1, G MUN5233DW1T1, G MUN5234DW1T1, G MUN5235DW1T1, G	-	-	-	0.25	
($I_C = 10 \text{ mA}$, $I_B = 1 \text{ mA}$)	MUN5211DW1T1, G MUN5212DW1T1, G MUN5213DW1T1, G MUN5214DW1T1, G MUN5236DW1T1, G MUN5230DW1T1, G MUN5231DW1T1, G MUN5237DW1T1, G MUN5215DW1T1, G MUN5216DW1T1, G MUN5232DW1T1, G MUN5233DW1T1, G MUN5234DW1T1, G MUN5235DW1T1, G	-	-	-	0.25	
Output Voltage (on) ($V_{CC} = 5.0 \text{ V}$, $V_B = 2.5 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$)	MUN5211DW1T1, G MUN5212DW1T1, G MUN5214DW1T1, G MUN5215DW1T1, G MUN5216DW1T1, G MUN5230DW1T1, G MUN5231DW1T1, G MUN5232DW1T1, G MUN5233DW1T1, G MUN5234DW1T1, G MUN5235DW1T1, G ($V_{CC} = 5.0 \text{ V}$, $V_B = 3.5 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$) ($V_{CC} = 5.0 \text{ V}$, $V_B = 5.5 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$) ($V_{CC} = 5.0 \text{ V}$, $V_B = 4.0 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
	MUN5213DW1T1, G MUN5236DW1T1, G MUN5237DW1T1, G	-	-	-	0.2	

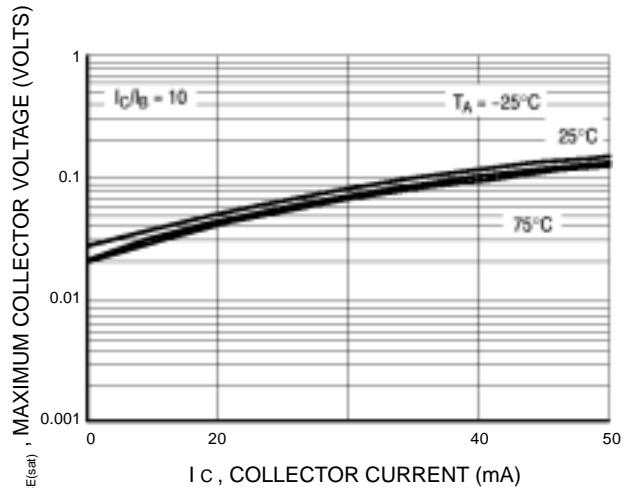
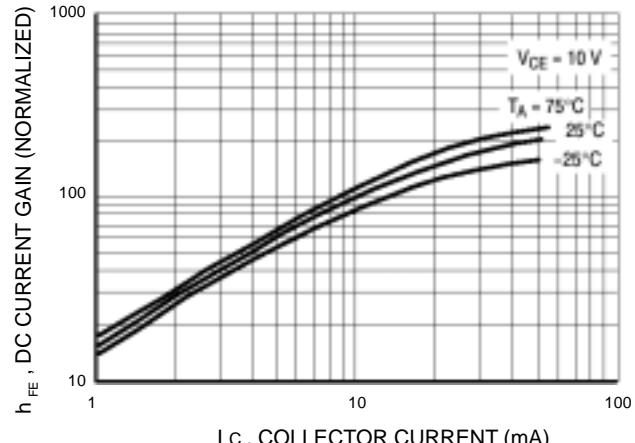
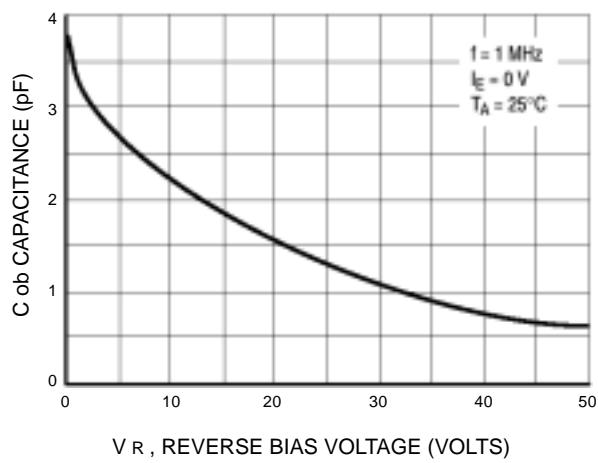
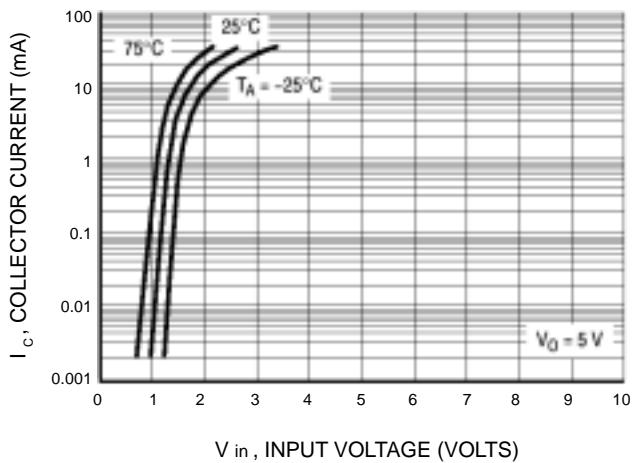
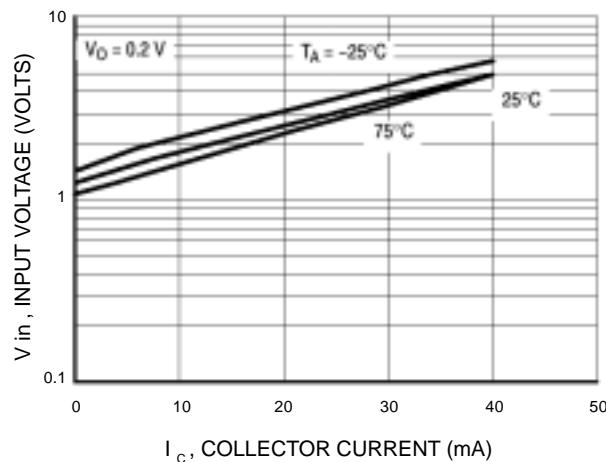
4. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

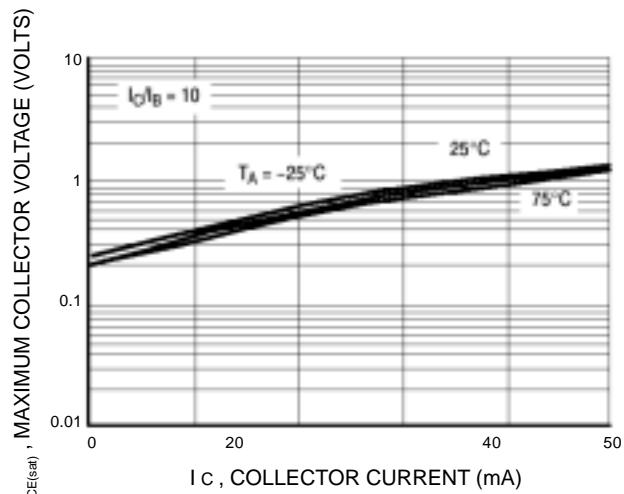
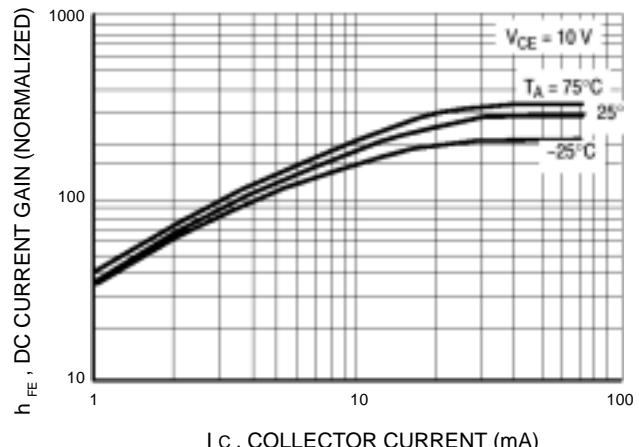
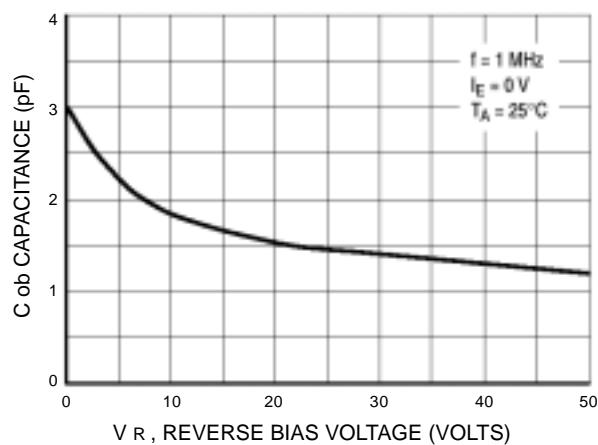
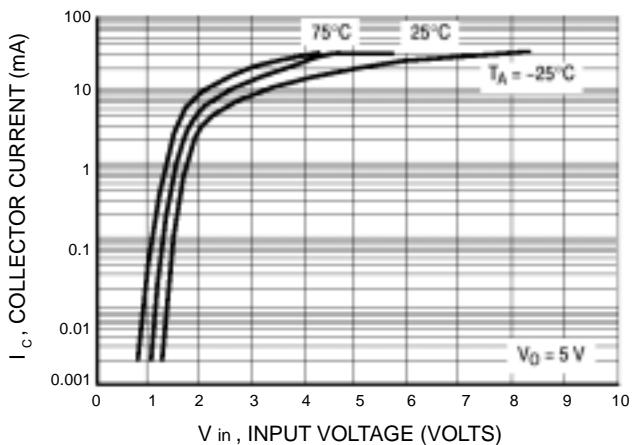
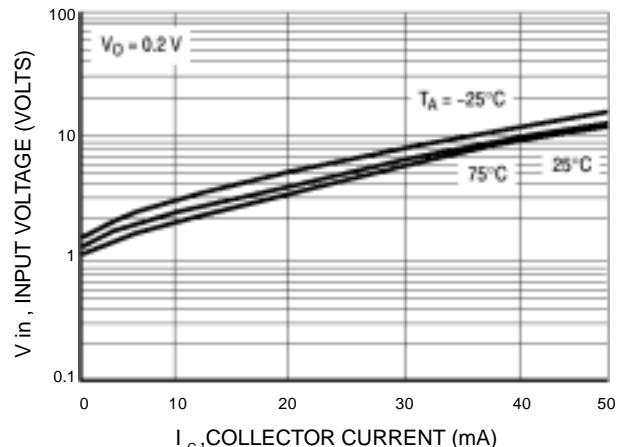
LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, common for Q₁ and Q₂.) (Continued)

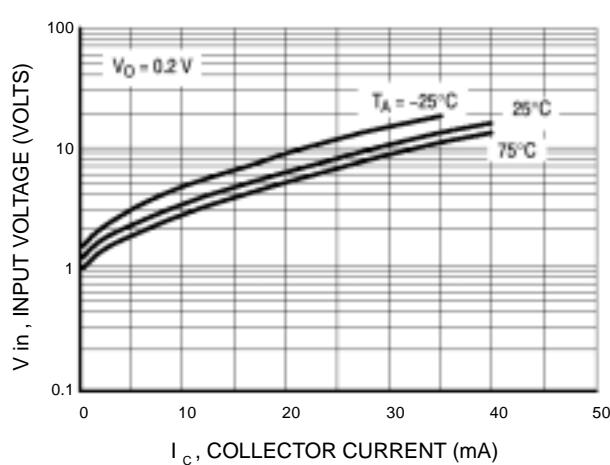
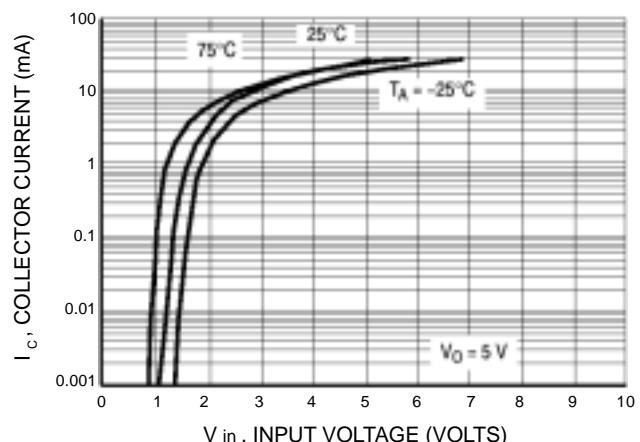
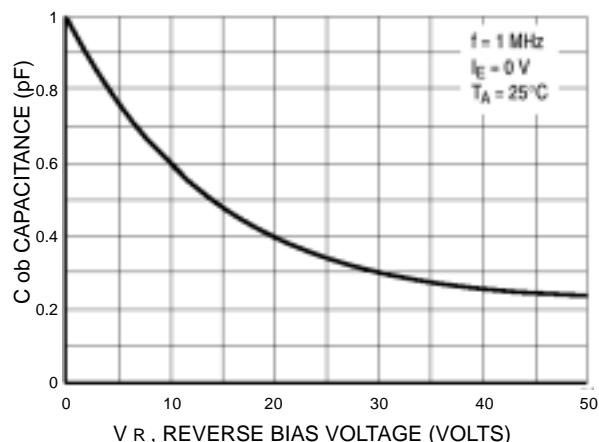
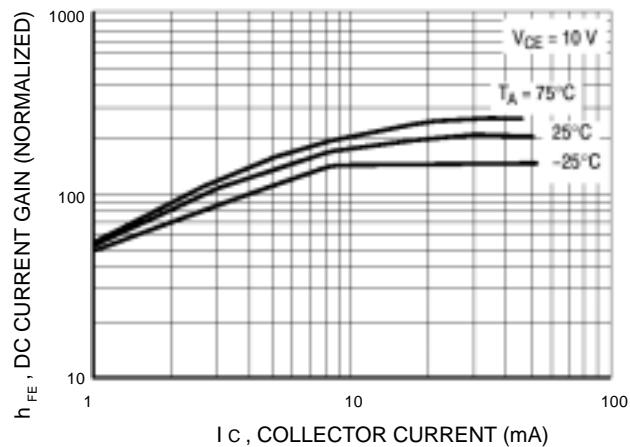
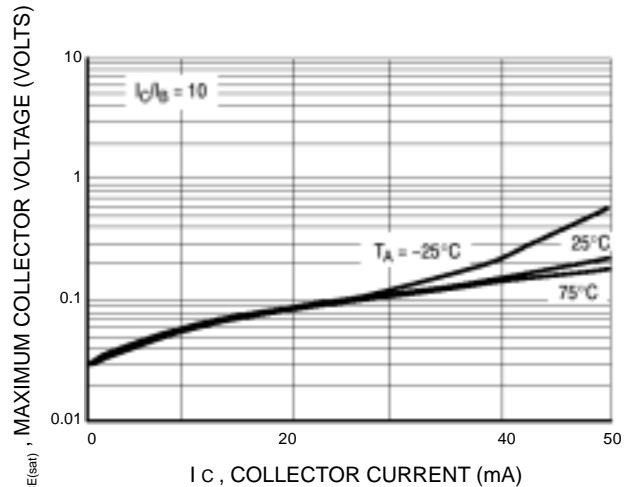
Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS (Note 5) (Continued)					
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 kΩ)	V _{OH}	4.9	—	—	Vdc
MUN5211DW1T1, G		4.9	—	—	
MUN5212DW1T1, G		4.9	—	—	
MUN5213DW1T1, G		4.9	—	—	
MUN5214DW1T1, G		4.9	—	—	
MUN5233DW1T1, G		4.9	—	—	
MUN5234DW1T1, G		4.9	—	—	
MUN5235DW1T1, G		4.9	—	—	
MUN5230DW1T1, G (V _{CC} = 5.0 V, V _B = 0.050 V, R _L = 1.0 kΩ)		4.9	—	—	
MUN5215DW1T1, G (V _{CC} = 5.0 V, V _B = 0.25 V, R _L = 1.0 kΩ)		4.9	—	—	
MUN5216DW1T1, G		4.9	—	—	
MUN5231DW1T1, G		4.9	—	—	
MUN5232DW1T1, G		4.9	—	—	
MUN5236DW1T1, G		4.9	—	—	
MUN5237DW1T1, G		4.9	—	—	
Input Resistor	R1	7.0	10	13	k Ω
MUN5211DW1T1, G		15.4	22	28.6	
MUN5212DW1T1, G		32.9	47	61.1	
MUN5213DW1T1, G		7.0	10	13	
MUN5214DW1T1, G		7.0	10	13	
MUN5216DW1T1, G		3.3	4.7	6.1	
MUN5230DW1T1, G		0.7	1.0	1.3	
MUN5231DW1T1, G		1.5	2.2	2.9	
MUN5232DW1T1, G		3.3	4.7	6.1	
MUN5233DW1T1, G		3.3	4.7	6.1	
MUN5234DW1T1, G		15.4	22	28.6	
MUN5235DW1T1, G		1.54	2.2	2.86	
MUN5236DW1T1, G		70	100	130	
MUN5237DW1T1, G		32.9	47	61.1	
Resistor Ratio MUN5211DW1T1, G/MUN5212DW1T1, G/ MUN5213DW1T1, G/MUN5236DW1T1, G	R1/R2	0.8	1.0	1.2	
MUN5214DW1T1, G		0.17	0.21	0.25	
MUN5215DW1T1, G/MUN5216DW1T1, G		—	—	—	
MUN5230DW1T1, G/MUN5231DW1T1, G/MUN5232DW1T1, G		0.8	1.0	1.2	
MUN5233DW1T1, G		0.055	0.1	0.185	
MUN5234DW1T1, G		0.38	0.47	0.56	
MUN5235DW1T1, G		0.038	0.047	0.056	
MUN5237DW1T1, G		1.7	2.1	2.6	

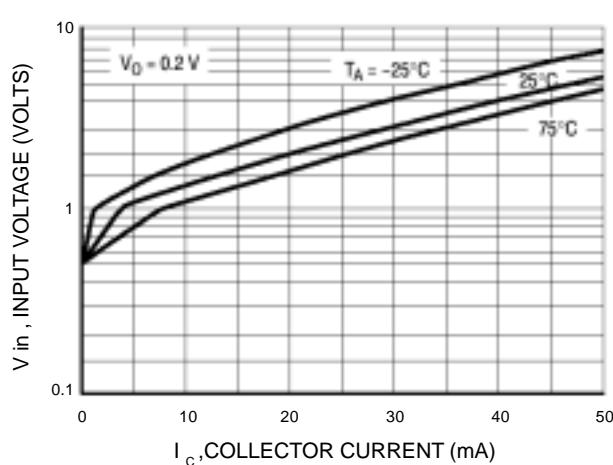
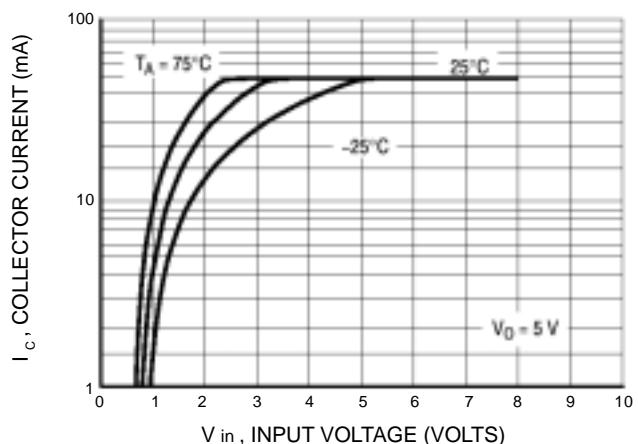
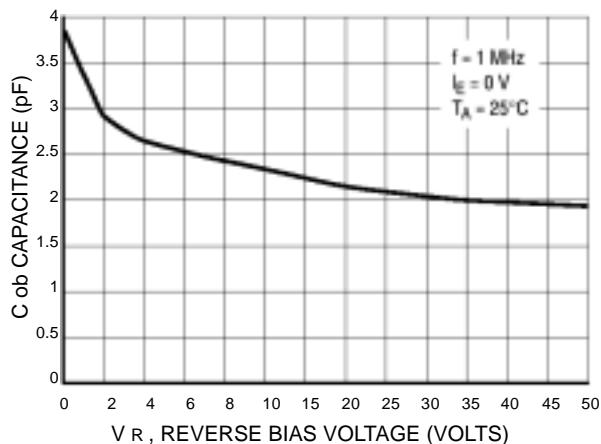
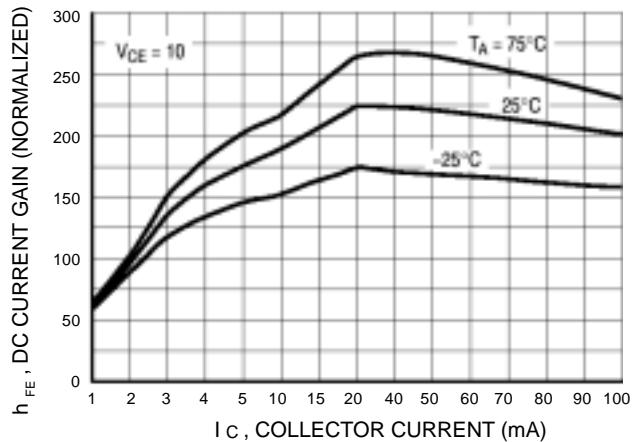
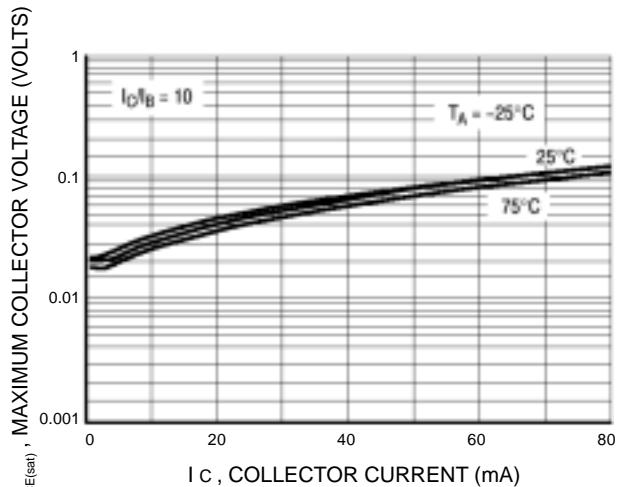
5. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

ALL MUN5211DW1T1 SERIES DEVICES

Figure 1. Derating Curve

LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
TYPICAL ELECTRICAL CHARACTERISTICS – LMUN5211DW1T1

Figure 2. $V_{CE(sat)}$ versus I_c

Figure 3. DC Current Gain

Figure 4. Output Capacitance

Figure 5. Output Current versus Input Voltage

Figure 6. Input Voltage versus Output Current

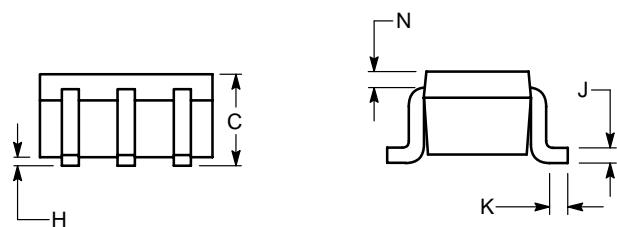
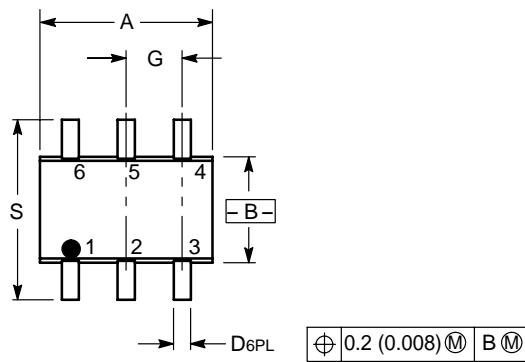
LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
TYPICAL ELECTRICAL CHARACTERISTICS – LMUN5212DW1T1

Figure 7. $V_{CE(sat)}$ versus I_C

Figure 8. DC Current Gain

Figure 9. Output Capacitance

Figure 10. Output Current versus Input voltage

Figure 11. Input Voltage versus Output Current

LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
TYPICAL ELECTRICAL CHARACTERISTICS – LMUN5213DW1T1


LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
TYPICAL ELECTRICAL CHARACTERISTICS – LMUN5214DW1T1


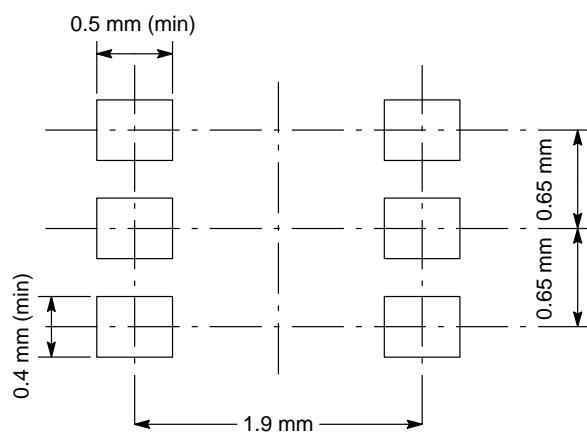
LMUN5211DW1T1G Series, S-LMUN5211DW1T1G Series
SC-88/SOT-363
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

PIN 1. Emitter 2
 2. Base 2
 3. Collector 1
 4. Emitter 1
 5. Base 1
 6. Collector 2



X-ON Electronics

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[DTC144VUAT106](#) [MUN5241T1G](#) [BCR158WH6327XTSA1](#) [NSBA114TDP6T5G](#) [SMUN5330DW1T1G](#) [SSVMUN5312DW1T2G](#)
[RN1303\(TE85L,F\)](#) [RN1306\(TE85L,F\)](#) [EMH15T2R](#) [SMUN2214T3G](#) [SMUN5335DW1T1G](#) [NSBC143ZPDP6T5G](#) [NSVDTA143ZET1G](#)
[SMUN2214T1G](#) [FMA7AT148](#) [DTC114EUA-TP](#) [SMUN5237DW1T1G](#) [SMUN5213DW1T1G](#) [SMUN5114DW1T1G](#) [SMUN2111T1G](#)
[DTC124ECA-TP](#) [DTA114ECA-TP](#) [DTC113EM3T5G](#) [NSVMUN5135DW1T1G](#) [NSVMUN2237T1G](#) [NSVDTC143ZM3T5G](#)
[SMUN5335DW1T2G](#) [SMUN5216DW1T1G](#) [NSVMUN5316DW1T1G](#) [NSVMUN5215DW1T1G](#) [NSVMUN5213DW1T3G](#)
[NSVMUN2112T1G](#) [NSVIMD10AMT1G](#) [NSVEMC2DXV5T1G](#) [NSVDTC144WET1G](#) [NSVDTC123JET1G](#) [NSVDTA143EM3T5G](#)
[NSVB1706DMW5T1G](#) [NSBC143EDP6T5G](#) [RN2101,LF\(CT](#) [NSBA144WDXV6T1G](#) [DTA115TET1G](#) [NSBC115TDP6T5G](#)